

## SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB01SHT12-CAL.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      05-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*      ALL RIGHTS RESERVED
*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB01SHT12-CAL SPICE Model
*
.SUBCKT GB01SHT12 ANODE KATHODE
R1 ANODE INT R=((TEMP-24)*0.0099); Temperature Dependant Resistor
D1 INT KATHODE GB01SHT12_25C; Call the 25C Diode Model
D2 ANODE KATHODE GB01SHT12_PIN; Call the PiN Diode Model
.MODEL GB01SHT12_25C D
+ IS      1.88E-18      RS      0.9255
+ N       1            IKF     98.29122743
+ EG      1.2          XTI     3
+ CJO     7.90E-11     VJ      0.367
+ M       1.63         FC      0.5
+ TT      1.00E-10     BV      1200
+ IBV     1.00E-03     VPK     1200
+ IAVE    1           TYPE     SiC_Schottky
+ MFG     GeneSiC_Semiconductor
.MODEL GB01SHT12_PIN D
+ IS      2.76E-16      RS      0.84243
+ N       3.791461     IKF     2.98675
+ EG      3.23         XTI     30
+ FC      0.5          TT      0
+ BV      1200         IBV     1.00E-03
+ VPK     1200         IAVE    1
+ TYPE    SiC_PiN
.ENDS
*
*      End of GB01SHT12-CAL SPICE Model
```